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FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE INDERMATION DISCLOSURE STATEMENT	ATTY, DOCKET NO. MICRON.198C1DV1	APPLICATION NO. 10/614,622
MAR 2 2 2004 N	APPLICANT Li, et al.	•
(USE EVERAL SHEETS IF NECESSARY)	FILING DATE July.7, 2003	GROUP 2812
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EXAMINER INITIAL	DOCUMENT NUMBE	ER DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)	
M	6,104,633	8/15/00	Abraham, et al.			Feb. 10, 1998	
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INITIAL						YES	Ю		
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EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)					
<i></i>	M. Durlam, et al. "A low power 1Mbit MRAM based on 1T1MTJ bit cell integrated with Copper Interconnects," 2002 Symposium on VLSI Circuits, Digest of Technical Papers (IEEE June 2002), pp. 158-161.					
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